

IN THE CLAIMS:

Please amend claim 1 as follows:

1. (Currently Amended) A method of manufacturing an electronic device comprising the steps of:

- (a) forming, on an underlying layer, an insulating film made from one of an oxide film, a nitride film, an oxide nitride film, an organic film and an organic-inorganic hybrid film;
- (b) forming a resist pattern on said insulating film;
- (c) forming an insulating film pattern by etching said insulating film with said resist pattern used as a mask;
- (d) conducting a plasma treatment on exposed portions of said underlying layer and said insulating film pattern without removing said resist pattern after the step (c); and
- (e) forming a pattern for said underlying layer by etching said underlying layer with said resist pattern and said insulating film pattern used as a mask after the step (d).

2. (Original) The method of manufacturing an electronic device of Claim 1, wherein said plasma treatment is conducted by using a gas including at least one of a N₂ gas, an O₂ gas and an inert gas in the step (d).

Claims 3-32 (Withdrawn)

REMARKS

The Official Action dated April 7, 2003 has been received and its contents carefully noted. In view thereof, claim 1 has been amended in order to better define that which Applicants regard as the invention. As previously, claims 1-32 are presently pending in the instant application, with claims 3-32 being withdrawn from further consideration by the Examiner as being directed to a non-elected invention.

With reference now to the Official Action, and particularly page 2 thereof, Applicant hereby acknowledges the election without traverse of claims 1 and 2 in connection with the present application.

With respect to the election of claims 1 and 2, it is Applicant's position that these claims define the invention as set forth by Applicants' claimed invention.

Specifically, as can be seen from the foregoing amendments, independent claim 1 has been